



BUK9880-55A/CUX Information



For Reference Only

Part Number BUK9880-55A/CUX **Manufacturer** Nexperia USA Inc.

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 55V 7A SOT223

Package TO-261-4, TO-261AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









BUK9880-55A/CUX Specifications

Manufacturer Part NumberBUK9880-55A/CUXManufacturerNexperia USA Inc.CategoryDiscrete Semiconductor ProductsPackageTO-261-4, TO-261AASeriesTrenchMOS?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)55VCurrent - Continuous Drain (Id) @ 25°C7A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ ImAGate Charge (Qg) (Max) @ Vds584pF @ 25VVgs (Max)±15VFET Feature-Power Dissipation (Max)8W (Tc)Rds On (Max) @ Id, Vgs73 mOhm @ 8A, 10VOperating Temperature-55°C ~ 150°C (TI)Mounting TypeSurface MountSupplier Device PackageSOT-223		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-261-4, TO-261AA Series TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C TA (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs T3 mOhm @ 8A, 10V Operating Temperature Mounting Type Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single TO-261-4, TO-261AA To-261AA To-261-4, TO-261AA To-261A	Manufacturer Part Number	BUK9880-55A/CUX
Transistors - FETs, MOSFETs - Single Package TO-261-4, TO-261AA Series TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 55V Current - Continuous Drain (Id) @ 25°C 7A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 2V @ ImA Gate Charge (Qg) (Max) @ Vgs 1lnC @ 5V Input Capacitance (Ciss) (Max) @ Vds 584pF @ 25V Vgs (Max) ±15V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 73 mOhm @ 8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type	Manufacturer	Nexperia USA Inc.
PackageTO-261-4, TO-261AASeriesTrenchMOS?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)55VCurrent - Continuous Drain (Id) @ 25°C7A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 1mAGate Charge (Qg) (Max) @ Vgs11nC @ 5VInput Capacitance (Ciss) (Max) @ Vds584pF @ 25VVgs (Max)±15VFET Feature-Power Dissipation (Max)8W (Tc)Rds On (Max) @ Id, Vgs73 mOhm @ 8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface Mount	Category	Discrete Semiconductor Products
Series TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 55V Current - Continuous Drain (Id) @ 25°C 7A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2V @ 1mA Gate Charge (Qg) (Max) @ Vgs 11nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 584pF @ 25V Vgs (Max) ±15V FET Feature Power Dissipation (Max) 8W (Tc) Rds On (Max) @ Id, Vgs 73 mOhm @ 8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount		Transistors - FETs, MOSFETs - Single
FET Type Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 55V Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type N-Channel 15V 74 (Tc) 75 V 84pF @ 25V 11nC @ 5V 84pF @ 25V 15V FET Feature	Package	TO-261-4, TO-261AA
Technology Drain to Source Voltage (Vdss) 55V Current - Continuous Drain (Id) @ 25°C 7A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 73 mOhm @ 8A, 10V Operating Temperature Surface Mount	Series	TrenchMOS?
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 7A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 73 mOhm @ 8A, 10V Operating Temperature Mounting Type Surface Mount	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Fundamental Surface Mount Fundamental Surface (Tis) A (Tc) 7A (Tc) 7	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 2V @ 1mA Gate Charge (Qg) (Max) @ Vgs 11nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 584pF @ 25V Vgs (Max) ETF Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 73 mOhm @ 8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type 4.5V, 10V 4.5V, 10V 4.5V, 10V 4.5V, 10V 4.5V, 10V 4.5V, 10V 584pF @ 25V 584pF @ 25V 784pF @ 25V 785pC ~ 150°C (TJ) Surface Mount	Drain to Source Voltage (Vdss)	55V
Vgs(th) (Max) @ Id 2V @ 1mA Gate Charge (Qg) (Max) @ Vgs 11nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 584pF @ 25V Vgs (Max) ±15V FET Feature - Power Dissipation (Max) 8W (Tc) Rds On (Max) @ Id, Vgs 73 mOhm @ 8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount	Current - Continuous Drain (Id) @ 25°C	7A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 584pF @ 25V Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 73 mOhm @ 8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds 584pF @ 25V Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 73 mOhm @ 8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount	Vgs(th) (Max) @ Id	2V @ 1mA
Vgs (Max)±15VFET Feature-Power Dissipation (Max)8W (Tc)Rds On (Max) @ Id, Vgs73 mOhm @ 8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface Mount	Gate Charge (Qg) (Max) @ Vgs	11nC @ 5V
FET Feature - Power Dissipation (Max) 8W (Tc) Rds On (Max) @ Id, Vgs 73 mOhm @ 8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount	Input Capacitance (Ciss) (Max) @ Vds	584pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 73 mOhm @ 8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount	Vgs (Max)	±15V
Rds On (Max) @ Id, Vgs73 mOhm @ 8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface Mount	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount	Power Dissipation (Max)	8W (Tc)
Mounting Type Surface Mount	Rds On (Max) @ Id, Vgs	73 mOhm @ 8A, 10V
	Operating Temperature	-55°C ~ 150°C (TJ)
Supplier Device Package SOT-223	Mounting Type	Surface Mount
	Supplier Device Package	SOT-223
Package / Case TO-261-4, TO-261AA	Package / Case	TO-261-4, TO-261AA
Report errors?		Report errors?

BUK9880-55A/CUX Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

BUK9880-55A/CUX Payment Methods



















BUK9880-55A/CUX Shipping Methods













If you have any question about BUK9880-55A/CUX, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com